CLAIMS

1. A method for cleaning a mask for vacuum vapor deposition, characterized by cleaning the mask with a cleaning composition containing at least one member selected from N-methyl-2-pyrrolidinone and N,N-dimethylformamide, and rinsing the mask after cleaning, with a rinsing composition containing CF_3CH_2-O-CF_2CHF_2 (HFE-347pc-f).

2. The cleaning method according to Claim 1, wherein the proportion of the content of the CF_3CH_2-O-CF_2CHF_2 in the rinsing composition is at least 80 mass% and at most 100 mass%.

3. The cleaning method according to Claim 1 or 2, wherein the cleaning composition contains N-methyl-2-pyrrolidinone.

4.. The cleaning method according to any one of Claims 1 to 3, wherein each of the cleaning and rinsing of the mask is conducted at a temperature of at least 10°C and at most 40°C.

5. The cleaning method according to any one of Claims 1 to 4, wherein each of the cleaning and rinsing of the mask is conducted at a temperature of at least 20°C and at most 30°C.

6. The cleaning method according to any one of Claims 1 to 5, wherein said vacuum vapor deposition is carried out in the production of a low-molecular type organic EL device.

7. The cleaning method according to any one of Claims 1 to 6, wherein the mask after being rinsed with the rinsing composition, is dried.